

Amendments to the Claims

Claims 1-40 (cancelled).

Claim 41 (new): A method of forming a conductive line comprising:

forming a silicon-comprising layer, the silicon-comprising layer comprising a dopant therein;

forming a silicide-comprising layer over the silicon-comprising layer;

after forming the silicide-comprising layer, out-diffusing dopant from the silicon-comprising layer to the silicide-comprising layer to provide the dopant to within the silicide-comprising layer to a concentration of at least 1×10^{18} ions/cm³; and

after the out-diffusing, etching the silicon-comprising layer and the silicide-comprising layer into a conductive line shape.

Claim 42 (new): The method of claim 41 wherein the silicide-comprising layer comprises one or more of tungsten, titanium, molybdenum, and cobalt.

Claim 43 (new): The method of claim 41 further comprising, after the out-diffusing, subjecting the silicide-comprising layer to a temperature of over 850°C for at least 10 seconds.

Claim 44 (new): The method of claim 41 further comprising, prior to the etching, forming an oxide layer over the silicide-comprising layer.

Claim 45 (new): The method of claim 44 wherein the forming the oxide layer over the silicide-comprising layer further comprises activating the dopant of the silicide-comprising layer.

Claim 46 (new): The method of claim 44 wherein the forming the oxide layer comprises subjecting the silicide-comprising layer to a rapid thermal processing step to exceed 850°C for at least 10 seconds while exposing the silicide-comprising layer to an oxygen-comprising atmosphere.

Claim 47 (new): The method claim 44 wherein the out-diffusing occurs after the forming of the oxide layer.

Claim 48 (new): The method of claim 41 wherein the conductive line comprises a wordline.

Claim 49 (new): A method of forming a conductive line comprising:

forming a silicon-comprising layer over a semiconductive substrate;

forming a silicide-comprising layer over the silicon-comprising layer, the silicide-comprising layer having a dopant concentration less than 1×10^{18} ions/cm³;

while the dopant concentration in the silicide-comprising layer is less than 1×10^{18} ions/cm³, etching the silicon-comprising layer and the silicide-comprising layer into a conductive line shape; and

after the etching, providing dopant within the silicide-comprising layer to a concentration greater than 1×10^{18} ions/cm³.

Claim 50 (new): The method of claim 49 wherein the silicide-comprising layer comprises one or more of tungsten, titanium, molybdenum, and cobalt.

Claim 51 (new): The method of claim 49 further comprising, before the etching, providing dopant to the silicon-comprising layer to a concentration of at least about 1×10^{19} ions/cm³.

Claim 52 (new): The method of claim 49 further comprising forming an oxide layer over the silicide-comprising layer prior to the etching, the silicide-comprising layer and the oxide layer having thickness, wherein the oxide layer thickness is less than one-half of the silicide-comprising layer thickness.

Claim 53 (new): The method of claim 52 further comprising, during the forming of the oxide layer, activating the dopant within the silicide-comprising layer.

Claim 54 (new): The method of claim 52 wherein the forming the oxide layer comprises subjecting the silicide-comprising layer to a rapid thermal processing step to exceed 850°C for at least 10 seconds while exposing the silicide-comprising layer to an oxygen-comprising atmosphere.

Claim 55 (new): The method of claim 49 further comprising, after the providing the dopant, forming source/drain regions within the semiconductive substrate.

Claim 56 (new): The method of claim 49 wherein the providing the dopant comprises gas phase chemical doping of the silicide-comprising layer.

Claim 57 (new): The method of claim 49 wherein the conductive line comprises a wordline.